ES52F3E50N-12.000M

Resistance to Soldering Heat

Resistance to Solvents

Temperature Cycling

Solderability

Vibration



ES52F3 E 50 N -12.000M

Series -3.3Vdc 14-Pin DIP Clipped Sinewave TCXO

Operating Temperature Range -40°C to +85°C

MIL-STD-202, Method 210

MIL-STD-202, Method 215

MIL-STD-883, Method 2003

MIL-STD-883, Method 1010

MIL-STD-883, Method 2007 Condition A

Frequency Stability ±5.0ppm Maximum

L Nominal Frequency 12.000MHz

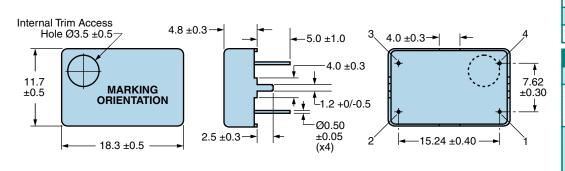
Control Voltage None (No Connect on Pin 1)

ELECTRICAL SPECIFICA	
Nominal Frequency	12.000MHz
Frequency Stability	±5.0ppm Maximum (Inclusive of Operating Temperature Range)
Frequency Stability vs. Input Voltage	±0.3ppm Maximum (±5%)
Aging at 25°C	±1ppm/Year Maximum
Frequency Stability vs. Load	±0.2ppm Maximum (±2pF)
Operating Temperature Range	-40°C to +85°C
Supply Voltage	3.3Vdc ±5%
Input Current	1.5mA Maximum
Output Voltage	0.7Vp-p Minimum
Load Drive Capability	10kOhms//10pF
Output Logic Type	Clipped Sinewave
Control Voltage	None (No Connect on Pin 1)
Internal Trim	±3ppm Minimum (Top of Can)
Modulation Bandwidth	10kHz Minimum (Measured at -3dB with a Control Voltage of 1.65Vdc)
Input Impedance	10kOhms Typical
Phase Noise	-70dBc at 10Hz Offset, -100dBc at 100Hz Offset, -130dBc at 1kHz Offset, -140dBc at 10kHz Offset, - 145dBc at 100kHz Offset
Storage Temperature Range	-40°C to +85°C
ENVIRONMENTAL & MEC	HANICAL SPECIFICATIONS
Fine Leak Test	MIL-STD-883, Method 1014 Condition A (Internal Crystal Only)
Gross Leak Test	MIL-STD-883, Method 1014 Condition C (Internal Crystal Only)
Lead Integrity	MIL-STD-883, Method 2004
Mechanical Shock	MIL-STD-202, Method 213 Condition C



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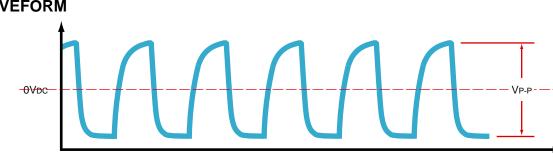
MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	No Connect
2	Case/Ground
3	Output
4	Supply Voltage
LINE	MARKING
1	ECLIPTEK
2	12.000M <i>M</i> =Nominal Frequency Unit of Measure
3	XXYZZ XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year

OUTPUT WAVEFORM

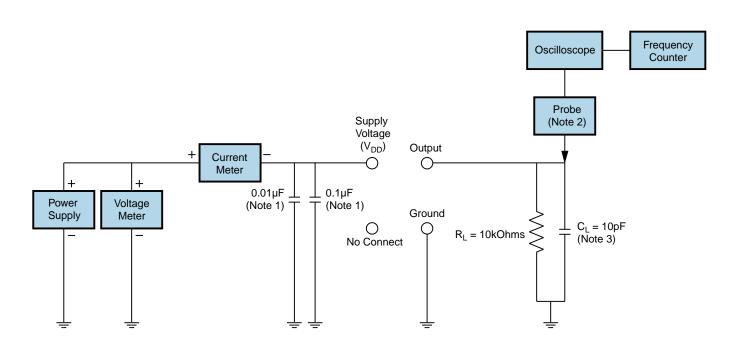
CLOCK OUTPUT



ES52F3E50N-12.000M



Test Circuit for No Connect Option



Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

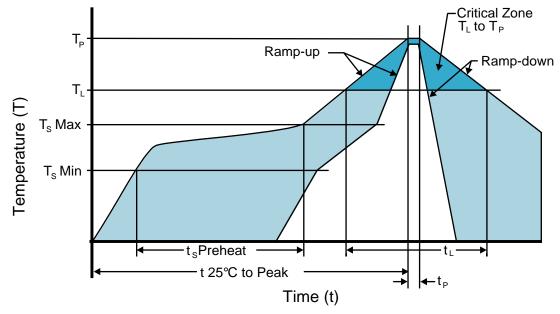
Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value \dot{C}_{L} includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods

ES52F3E50N-12.000M



Low Temperature Solder Bath (Wave Solder)

•
5°C/second Maximum
N/A
150°C
N/A
30 - 60 Seconds
5°C/second Maximum
150°C
200 Seconds Maximum
245°C Maximum
245°C Maximum 1 Time / 235°C Maximum 2 Times
5 seconds Maximum 1 Time / 15 seconds Maximum 2 Times
5°C/second Maximum
N/A
Level 1

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum.

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum.

Low Temperature Solder Bath (Wave Solder) Note 1

Device is non-hermetic; Post reflow aqueous wash is not recommended

Low Temperature Solder Bath (Wave Solder) Note 2

Temperatures shown are applied to back of PCB board and device leads only.